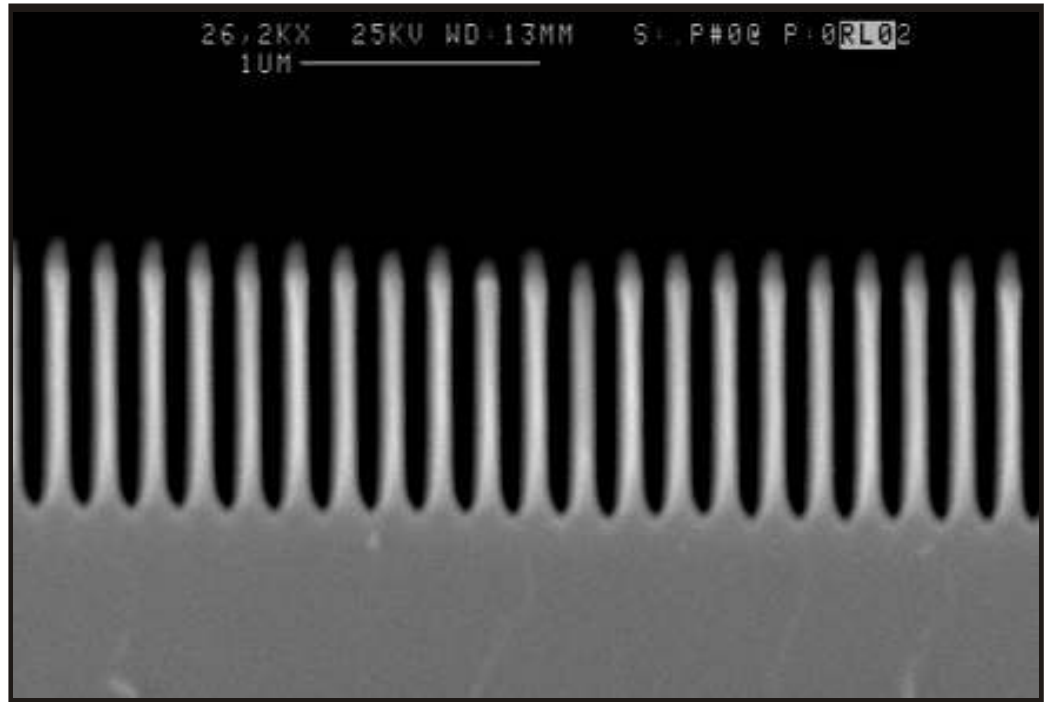
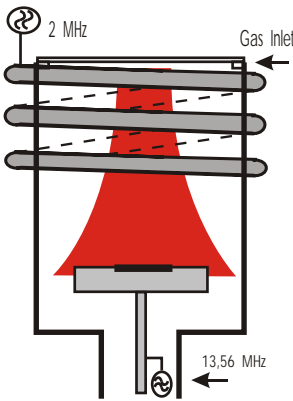


# Plasmalab Data

## 100 nm gratings etched in Si at 10 : 1 aspect ratio



*Plasmalab 80 Plus*  
*Plasmalab System 100*  
*Plasmalab System 133*

100 nm lines etched at 10 : 1 aspect ratio



**Technology:**

- Inductive Coupled Plasma - RIE
- 13 MHz induced RF bias
- Fluorine based low temperature process

**Results:**

- etch rate : 230 nm / min
- selectivity to e beam resist: 7.7 : 1
- good uniformity over 4" wafer